



**SiC - photodiode JEC 0,1SHT/
JEC 0,1SSHT**



- characteristics :**
- ◆ spectral range 210 ... 380 nm
 - ◆ active arrea 0,055 mm²
 - ◆ high UV-responsivity 0,13 A/W
 - ◆ TO 18-package
 - ◆ suitable for operating temperatures up to 150 °C
 - ◆ components are in conformity with RoHS and WEEE

- applications :**
- ◆ UV-measurements only
 - ◆ UV-source control
 - ◆ flame detection

maximum ratings:

reverse voltage 20 V
operating temperature range- 25 °C ... +150 °C
storage temperature range -40 °C ... +150 °C
soldering temperature (3s) 260 °C

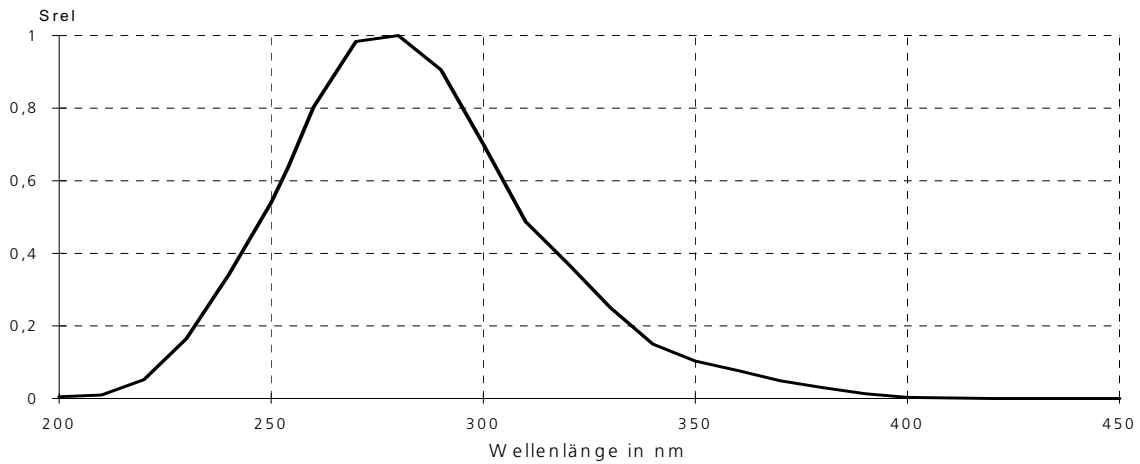
technical data :

test conditions, as not otherwiuse specified: $\gamma_a = 25 \text{ °C}$, $V_R = 0V$

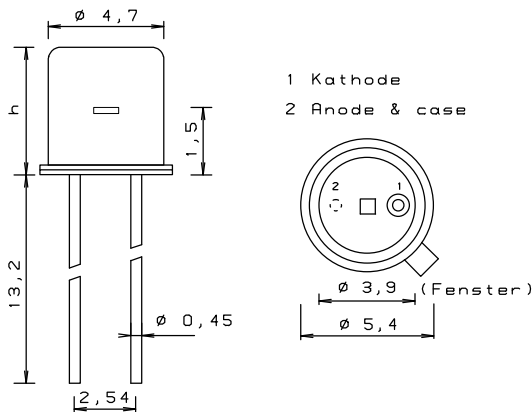
parameter	test condition	min.	typ.	max.	unit
active area			0,25 x 0,25		mm ²
spectral range		210		380	nm
maximumof spectral responsivity	$\lambda_{max} = 275 \text{ nm}$		0,13		A/W
absolute spectral responsivity	$\lambda = 254 \text{ nm}$		0,11		A/W
dark current I_R	$V_R = 1 \text{ V}$		1		fA
capacitance			21		pF

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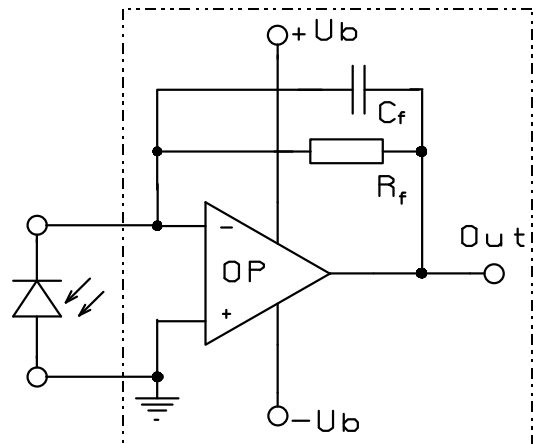
relative spectral responsivity



package dimensions



application example



JEC 0,1SHT $h = 5,2$ mm
 JEC 0,1SSHT $h = 3,7$ mm

The application example shows a typical circuit.. R_f is responsible for the gain of the circuit. C_f compensates the reverse junction capacitance of the photodiode and input capacitance of the OPV. The exact value of C_f depends on R_f , used OPV and capacitance of the circuit. A typical value is 1 pF.

The diagram shows dependence of amplitude of the application circuit with OPA 111, $R_f = 50$ M Ω and $C_f = 0.5$ pF.

